

2.5V Drive Nch + Nch MOSFET

EM6K31

Structure

Silicon N-channel MOSFET

Features

1) High speed switing.

2) Small package(EMT6).

3) Low voltage drive(2.5V drive).

Application

Switching

Packaging specifications

_		
Туре	Package	Taping
	Code	T2R
	Basic ordering unit (pieces)	8000
EM6K31		0

• Absolute maximum ratings (Ta = 25°C)

		/		
Param	eter	Symbol	Limits	Unit
Drain-source voltage		V _{DSS}	60	V
Gate-source voltage		V _{GSS}	±20	V
Drain current	Continuous	I _D	±250	mA
	Pulsed I _{DP} ^{*1} ±1	±1	А	
Source current	Continuous	l _s	125	mA
(Body Diode)	Pulsed	۱ _{sp} *1	1	А
Power dissipation		P _D *2	150	mW / TOTAL
		т <u>р</u> –	120	mW / ELEMENT
Channel temperature		Tch	150	°C
Range of storage tem	perature	Tstg	-55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%

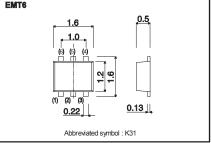
*2 Each terminal mounted on a recommended land.

• Thermal resistance

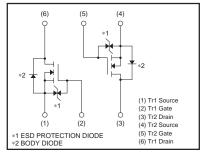
Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)	833	°C / W /TOTAL
	Kui (cii-a)	1042	°C / W /ELEMENT

* Each terminal mounted on a recommended land.

• Dimensions (Unit : mm)



• Inner circuit



• Electrical characteristics (Ta = 25°C)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	-	±10	μA	V_{GS} =±20V, V_{DS} =0V
Drain-source breakdown voltage	V _{(BR)DSS}	60	-	-	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	-	-	1	μA	V _{DS} =60V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	1.0	-	2.3	V	V _{DS} =10V, I _D =1mA
		-	1.7	2.4	Ω	I_D =250mA, V_{GS} =10V
Static drain-source on-state	P*	-	2.1	3.0		I _D =250mA, V _{GS} =4.5V
resistance	R _{DS (on)}	-	2.3	3.2		I _D =250mA, V _{GS} =4.0V
		-	3.0	12.0		I _D =10mA, V _{GS} =2.5V
Forward transfer admittance	۱ Y _{fs} I*	0.25	-	-	S	I _D =250mA, V _{DS} =10V
Input capacitance	C _{iss}	-	15	-	pF	V _{DS} =25V
Output capacitance	C _{oss}	-	4.5	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	-	2.0	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	3.5	-	ns	I _D =100mA, V _{DD} ≒30V
Rise time	t _r *	-	5	-	ns	V _{GS} =10V
Turn-off delay time	t _{d(off)} *	-	18	-	ns	R _L ≒300Ω
Fall time	t _f *	-	28	-	ns	R _G =10Ω

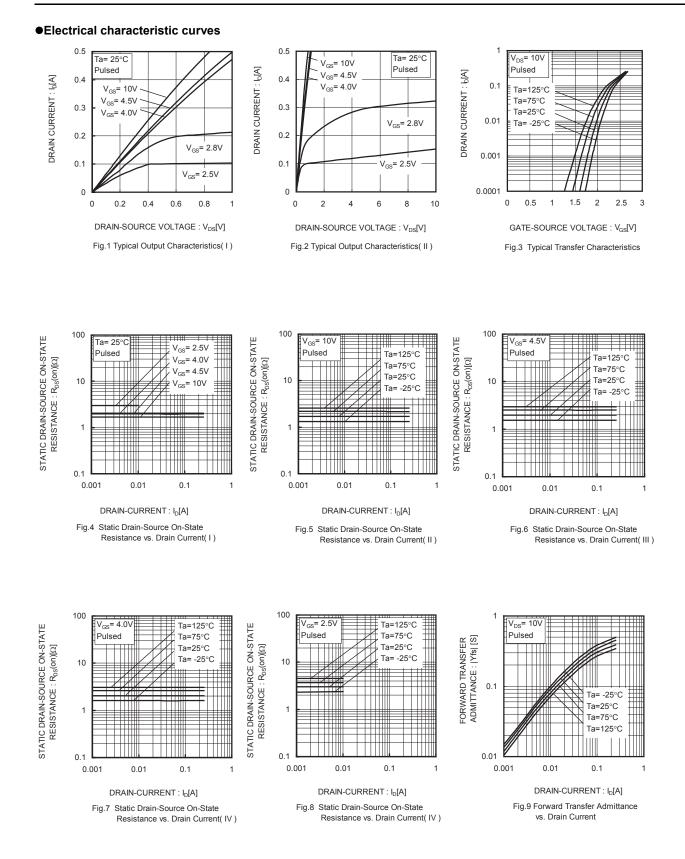
*Pulsed

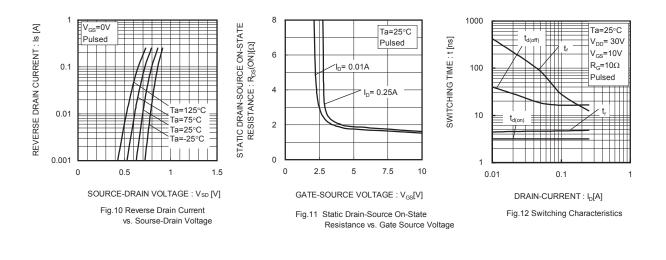
•Body diode characteristics (Source-Drain) (Ta = 25°C)

< It is the same ratings for Tr1 and Tr2.>

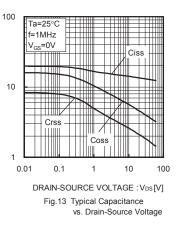
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V_{SD}^{*}	-	-	1.2	V	I _s =250mA, V _{GS} =0V

*Pulsed





CAPACITANCE : C [pF]



Measurement circuits

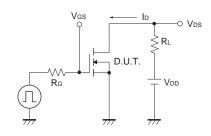


Fig.1-1 Switching time measurement circuit

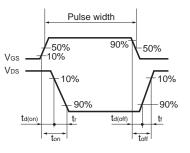


Fig.1-2 Switching waveforms

Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

	copying or reproduction of this document, in part or in whole, is permitted without the nsent of ROHM Co.,Ltd.
The	e content specified herein is subject to change for improvement without notice.
"Pr	e content specified herein is for the purpose of introducing ROHM's products (hereinafte oducts"). If you wish to use any such Product, please be sure to refer to the specifications ich can be obtained from ROHM upon request.
illu	amples of application circuits, circuit constants and any other information contained herein strate the standard usage and operations of the Products. The peripheral conditions mus taken into account when designing circuits for mass production.
Ho	eat care was taken in ensuring the accuracy of the information specified in this document wever, should you incur any damage arising from any inaccuracy or misprint of such prmation, ROHM shall bear no responsibility for such damage.
exa imp oth	e technical information specified herein is intended only to show the typical functions of an amples of application circuits for the Products. ROHM does not grant you, explicitly o plicitly, any license to use or exercise intellectual property or other rights held by ROHM and er parties. ROHM shall bear no responsibility whatsoever for any dispute arising from the e of such technical information.
equ	e Products specified in this document are intended to be used with general-use electronic upment or devices (such as audio visual equipment, office-automation equipment, commu ation devices, electronic appliances and amusement devices).
The	e Products specified in this document are not designed to be radiation tolerant.
	ile ROHM always makes efforts to enhance the quality and reliability of its Products, a oduct may fail or malfunction for a variety of reasons.
aga fail sha	ase be sure to implement in your equipment using the Products safety measures to guard ainst the possibility of physical injury, fire or any other damage caused in the event of the ure of any Product, such as derating, redundancy, fire control and fail-safe designs. ROHM all bear no responsibility whatsoever for your use of any Product outside of the prescribed ope or not in accordance with the instruction manual.
sys ma ins cor of	e Products are not designed or manufactured to be used with any equipment, device o stem which requires an extremely high level of reliability the failure or malfunction of which y result in a direct threat to human life or create a risk of human injury (such as a medica trument, transportation equipment, aerospace machinery, nuclear-reactor controller, fuel- ntroller or other safety device). ROHM shall bear no responsibility in any way for use of any the Products for the above special purposes. If a Product is intended to be used for any ch special purpose, please contact a ROHM sales representative before purchasing.
be	rou intend to export or ship overseas any Product or technology specified herein that may controlled under the Foreign Exchange and the Foreign Trade Law, you will be required to tain a license or permit under the Law.



Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/